MIL-S-19500/207C(EL)

9 December 1966

SUPERSEDING
MIL-S-19500/207B(EL)

13 October 1966

MILITARY SPECIFICATION

TRANSISTOR, NPN, SILICON TYPES 2N1479, 2N1480, 2N1481, 2N1482

1. SCOPE

- 1.1 Scope. This specification covers the detail requirements for silicon, NPN, medium-power transistors for use in compatible equipment circuits. (See 3.4 and 6.2 herein.)
 - 1.2 Outline and dimensions. See Figure 1 herein. (TO-5)
 - 1.3 Maximum ratings.-

	P _T 1/	V _{CBO}	VCEO	V _{CEX}	V _{EBO}	I _B	lc	TJ	θ _{J-C}	Tstg
	W	Vdc	Vdc	Vdc	Vdc	Adc	Adc		°C/W	°C
2N1479	T	60	40	60	12	1.0	1.5	+200	35	-65to+200
2N1480	1	100	5 5	100	12	1.0	1.5	+200	35	-65to+200
2N1481	1	60	40	60	12	1.0	1.5	+200	35	-65to+200
2N1482	1	100	55	100	12	1.0	1.5	+200	35	-65to+200

This power dissipation is for 1000 hours expected life at $T_A = +25$ °C.

1.4 Particular electrical characteristics. - (at TA = +25°C, unless otherwise specified):

	at: 1 _C =2(^h FE 00 mAdc =4 Vdc	lc=20	0 mAdc	V _{CE} =4)mAdc Vdc	CB ^O CB ⁼³		ot: VEB=1	O 2 Vdc	fab at: V _{CB} =2 I _C = 5	8 Vdc
	Min =	Max	Vo Min		Vd Min	<u>c</u> Max	uAd Min	Max	uAd Min	c Max	kH: Min	Max
2N1479	20	60		Max 0.75		1.5		5	41111	10	800	Max
2N1480	20	60		0.75		1.5		5		10	800	
2N1481	35	100		0.75		1.5		5		10	800	
2N1482	35	100		0.75		1.5		5		10	800	

 $\frac{1}{4}$ At $I_B = 20$ mAdc for 2N1479, 2N1480; at $I_B = 10$ mAdc for 2N1481, 2N1482.

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2. APPLICABLE DOCUMENTS

2.1 The following documents, of the issue in effect on date of invitation for bids or request for proposal, form a part of this specification to the extent specified herein:

SPECIFICATIONS

MILITARY

MIL-S-19500

Semiconductor Devices, General Specification For

STANDARDS

MILITARY

MIL-STD-202

Test Methods For Electronic and Electrical Component Parts

MIL-STD-750

Test Methods For Semiconductor Devices

(Copies of specifications, standards, drawings, and publications required by contractors in connection with specific procurement functions should be obtained from the procuring agency or as directed by the contracting officer. Both the title and number or symbol should be stipulated when requesting copies.)

3. REQUIREMENTS

- 3.1 Requirements Requirements for the transistors shall be in accordance with Specification MIL-S-19500 and as otherwise specified herein.
- 3.2 Abbreviations and symbols. The abbreviations and symbols used herein are defined in Specification MIL-S-19500, and as follows:

 t_{off} ($t_s + t_f$)

-9- 3.3 Design and construction. - The transistor shall be of the design, construction, and physical dimensions specified on Figure 1. (See 3.3.2 herein.)

- 3.3.1 Terminal arrangement. The terminal arrangement on the transistor shall be as indicated in Figure 1.
- 3.3.2 Terminal-lead length. Terminal-lead length(s) other than that specified in Figure 1 may be furnished under contract or order (see 6.3 herein) when the devices covered herein are required directly for particular equipment-circuit installation or for automatic-assembly-technique programs. Where such longer leads are required and provided, it shall not be construed as affecting adversely the Qualified-product status of the device, or applicable JAN marking.
- -9- 3.3.3 Operating position. The transistor shall be capable of proper operation in any position.
- 3.4 Performance characteristics.— The transistor performance characteristics shall be as specified in Tables I, II, and III herein. Except where specifically differentiated for respective transistor types (see 1.3, 1.4, and Tables I, II, and III herein), the performance requirements, including characteristics, ratings, and test conditions, apply equally to all transistor types covered herein.
- 3.5 Marking. Except as otherwise specified herein, marking shall be in accordance with Specification MIL-S-19500. If any specification-requirements waiver has been granted, the product-identification marking shall consist of the 'classification' type designation only. The 'manufacturer's identification' and 'country or origin' may, at option of the manufacturer, be omitted from being marked directly on the semiconductor device coverdd herein. (See 3.3.2 and 4.3.4 herein.)

4. QUALITY ASSURANCE PROVISIONS

- 4.1 General. Except as otherwise specified herein, the responsibility for inspection, general procedures for acceptance, classification of inspection, and inspection conditions and methods of test shall be in accordance with Specification MIL-S-19500, Quality Assurance Provisions.
- 4.1.1 Procedure for lots held more than 1 year. The requirements in Specification MIL-S-19500, paragraph 4.2, applicable to "lots held more than 6 months" shall apply, herewith, only to lots held more than 1 year.
- 4.2 Qualification and acceptance inspection.— Qualification and Quality Conformance inspection shall be in accordance with Specification MIL-S-19500, Quality Assurance Provisions, and as otherwise specified herein (see 4.2.2 herein). Groups A, B, and C inspection shall consist of the examinations and tests specified in Table I, II and III, respectively, herein. Quality Conformance inspection shall include inspection of Preparation for Delivery (see 5.1 herein).
 - 4.2.1 Specified LTPD for subgroups.— The LTPD specified for a subgroup in Table I, II, and III herein shall apply for all of the tests, combined, in the subgroup.
 - 4.2.2 Group B-Group C life test samples. Samples that have been subjected to Group B, 340-hour life test may be continued on test for 1000 hours in order to satisfy Group C life test requirements. These samples shall be predesignated, and shall remain subjected to the Group C 1000-hour evaluation after they have passed the Group B, 340-hour acceptance criteria. The cumulative total of failures found during the subsequent interval up to 1000 hours shall be computed for 1000-hour acceptance criteris. (See 4.2.3 herein.)

- 4.2.3 Group C testing. Unless otherwise specified, Group C tests shall be performed on the initial lot and thereafter on a lot every 6 months. (See Table III herein.) The contractor shall, throughout the course of a contract or order, permit the Government representative to scrutinize all test data and findings covering manufacturer's test program on Group C characteristics and parameters for the product concerned. Upon determination by the Government inspector (in advance of Group C, 6-month, test results) that Group C parameters are not being adequately met, the Government inspector may require lot-by-lot inspection, normally for a minimum of 3 consective lots, to be performed for required Group C tests.
- 4.2.4 Disposition of sample units. Sample units that have been subjected to Group B, Subgroup 2, 4, and 5 tests shall not be delivered on the contract or order. Sample units that have been subjected to and have passed Group B, Subgroups 1, 3, 6, 7 and 8 tests and all Group C tests, (these tests to be considered non-destructive) may be delivered on the contract or order provided that, after Group B inspection is terminated, those sample units are subjected to and pass Group A inspection. Defective units from any sample group that may have passed group inspection shall not be delivered on the contract or order until the defect(s) has been remedied to the satisfaction of the Government.
 - 4,3 Particular examination and test requirements.
- 4.3.1 Interval for End-Point Test measurements. All applicable End-Point Test measurements shall be performed after sample units have been subjected to required physical-mechanical or environmental test(s), in accordance with the following time-delay limitations:
 - (a) For Qualification inspection: within 24 hours.
 - (b) For Quality Conformance inspection: within 96 hours; however, at discretion of the Government inspector, a more protracted interval may be allowed.
- 4.3.2 Shock.— The shock testing apparatus shall be capable of providing shock pulses of the specified peak acceleration, waveform, and pulse duration to the body of the device. The acceleration pulse, as determined from the unfiltered output of a transducer with a natural frequency greater than 10,000 cycles per second, shall be a half-sine waveform with an allowable distortion not greater than ± 20 percent of the specified peak acceleration. The pulse duration shall be measured between the points at 10 percent of the peak acceleration during rise and at 10 percent of the peak acceleration during decay. Absolute tolerance of the pulse duration shall be ± 30 percent of the specified duration.
- 4.3.5 <u>Mechanical damage resulting from tests.</u> Except for intentionally deforming, mutilating, or dismembering mechanical-stress tests to which samples are subjected, there shall be no evidence of mechanical damage to any sample unit as a result of any of the Groups A, B, or C tests.
 - 4.3.4 Marking legibility. Marking shall be legible before and after all tests.

Table I. Group A inspection.

Test Method per	Examination or test	Conditions	LTPD Symbo	Ι [Limits	
MIL-STD-750	1/		. : .	Min	Max	•
	Subgroup 1		10	*****		
2071	Visual and mechanical examination					
	Subgroup 2		5			
3036	Collector-base cutoff current:	Bias Cond. D				
	2N1479, 2N1481 2N1480, 2N1482	V _{CB} = 30 Vdc V _{CB} = 50 Vdc	I _{CBO} ICBO		5 5	uAdc uAdc
3061	Emitter-base cutoff current	Bias Cond. D V _{EB} = 12 Vdc	EBO	***	10	uAdc
3011	Collector-emitter breakdown voltage:	Bias Cond. D I _C = 50 mAdc				
	2N1479, 2N1481 2N1480, 2N1482		BV BVCEO CEO	40 55		Vdc Vdc
3011	Collector-emitter breakdown voltage, emitter-to-base reversed biased:	Bias Cond. A I _C = 0.25 mAdc V _{EB} = 1.5 Vdc				
	2N1479, 2N1481 2N1480, 2N1482		BV _{CEX}	60 100		Vdc Vdc

Table 1. Group A inspection.-(Cont'd)

Test Method per	Examination or test	Conditions	LTPD	Symbol		nits [.]	Unit
MIL-STD-750	<u>1</u> /			, ,	Min	Max	
	Subgroup 3		5				
3076	Static forward-current transfer ratio:	l _C = 200 mAdc V _{CE} = 4 Vdc					
	2N1479, 2N1480 2N1481, 2N1482			h _{FE} h _{FE}	20 35	60 100	
3071	Collector-emitter saturation voltage:	I _C = 200 mAde					
	2N1479, 2N1480 2N1481, 2N1482	$l_{B} = 20 \text{ mAdc}$ $l_{B} = 10 \text{ mAdc}$		V _{CE} (sat) V _{CE} (sat)			
3066	Base-to-emitter voltage	Test Cond. B I _C = 200 mAdc V _{CE} = 4 Vdc		V _{BE}	*****	1.5	Vdc
	Subgroup 4	:	5	•			
3301	Small-signal short-circuit forward-current transfer-ratio cutoff frequency	$I_C = 5 \text{ mAdc}$ $V_{CB} = 28 \text{ Vdc}$		f _{ab}	800		KHz
3251	Total switching time	$R_{C} = 59 \text{ ohms}$ $V_{CC} = 12 \text{ Vdc}$ $I_{B(o)} = I_{B(2)} = 8.5 \text{ mAdc}$ $I_{B(1)} = 20 \text{ mAdc}$		(t _{on} + toff		2 5	usec

Nee 3.4 herein.

Table II. Group B inspection.

Test Method per MIL-STD-750	Examination or test	Conditions	LTPD Symbol		nits Max	Unit
	Subgroup 1		20			
2066	Physical dimensions					
	Subgroup 2		10			
® - 2026	Solderability	Omit aging	*==			
1051	Temperature cycling	Test Cond. C 10 cycles				~~~
1056	Thermal shock (glass strain)	Test Cond. A				***
<u>2</u> /	Seal (leak rate)	Test Cond. C, procedure III; Test Cond. A for gross leaks	•		10 ⁻⁷	atm cc/sec
1021	Moisture resistance	-	***			
3036	End-point tests: Collector-base cutoff current:	Bias Cond. D				
	2N1479, 2N1481 2N1480, 2N1482	$V_{CB} = 30 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$	I _{CBO}		5. 5	uAdc uAdc
3076	Static forward-current transfer ratio:	$I_C = 200 \text{ mAdc}$ $V_{CE} = 4 \text{ Vdc}$				
	2N1479, 2N1480 2N1481, 2N1482		h _{FE} hFE	20 35	60 100	

Table II. Group B inspection-(Cont'd)

Test Method per MIL-STD-750	1/				4 4 *		Unit
					Min	Max	
	Subgroup 3		10			4	
2016	Shock	3/ Non-operating		~			
		G = 500 5 blows of 1.0 msec ea. in orientations X1, Y1, Y2, Z1 (total = 20 blows)					
2046	Vibration fatigue	Non-operating					100 ma em
2056	Vibration, variable frequency						
2006	Constant acceleration (centrifugal)	10,000G Orientations X1, Y1, Y2, Z1		and the gar	~==	~	-
	End-point tests: Same as for Subgroup 2 a	bove					
	Subgroup 4		20				
- 2036	Terminal strength (lead fatigue)	Test Cond. E					
	End-point tests: Same as for Subgroup 2 a	bove				-	
	Subgroup 5		20				
1041	Salt atmosphere (corrosion))					
	End-point tests: Same as for Subgroup 2 al	bove					
<u>5</u> /	Subgroup 6 47 High-temperature operation:	$T_{A} = +175^{\circ} _{-0^{\circ}}^{+5^{\circ}} C$	15				
3 036	Collector-base cutoff current:	Bias Cond. D					
	2N1479, 2N1481 2N1480, 2N1482	V _{CB} =30 Vdc V _{CB} =50 Vdc	I I	CBO CBO			mAdo
		ġ					

Table II. Group B inspection-(Cont'd)

Test Method per	Examination or test	Conditions	LTPD	Symbol		mits	Unit
MIL-STD-750	1/			•	Min	Max	
	Subgroup 6 4/_ (Co	ont 'd)				_	
<u>5</u> /	Low-temperature operation:	$T_A = -55^{\circ}_{+0}^{-3}$ ° C					
3076	Static forward- current transfer ratio:	$I_C = 200 \text{ mAdc}$ $V_{CE} = 4 \text{ Vdc}$					
	2N1479, 2N1480 2N1481, 2N1482 Subgroup 7	v	10	hfE hfE	10 17		***
1031	High-temperature life (non-operating)	T _{stg} = +200°C t = 340 hours <u>6</u> /					
3036	End-point tests: Collector-base cutoff current:	Bias Cond. D					
	2N1479, 2N1481 2N1480, 2N1482	$V_{CB} = 30 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$		I _{CBO}		10 10	uAdc uAdc
3076	Static forward-current transfer ratio: 2N1479, 2N1480 2N1481, 2N1482 Subgroup 8	I _C = 200 mAdc V _{CE} = 4 Vdc	10	hFE hFE	15 25	75 125	(p. 10 411
1026	Steady-state operation life:	T _A = +25°C V _{CE} = 28 Vdc P _T = 1.0 W t = 340 hours 6/			444	-	
	End-point tests: Same as for Subgroup 7 at				_		

See 3.4 and 4.3.1 herein.

Per Method 112 in Standard MIL-STD-202.

For this Subgroup, the sample units subjected to the High-Temp. Oper. test shall be permitted to return to and be stablized at room ambient temperature prior to their being subjected to the Low-Temp. Oper. test.

^{3/} See 4.3.2 herein.

Measurement(s) shall be made after thermal equilibrium has been reached at the temperature specified.

See 4.2.2 herein.

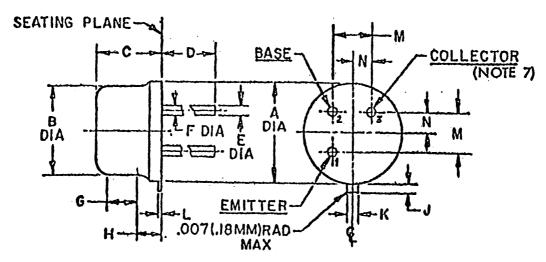
Table III. Group C inspection. 1/

Test Method per	Examination or test	Conditions	LTI	D Symbol	L	imit	Unit
MIL-STD-750	<u>2</u> /			7		Max	
•	Subgroup 1		20				
1001	Barometric pressure, reduced (altitude operation):	Pressure=8±2 mmHg Normal mounting t = 1 minute, minimu	ηm	****	00 00 00		
3036	Measurement during test: Collector-to-base cutoff current:	Bias Cond. D					
	2N1479, 2N1481 2N1480, 2N1482	V _{CB} = 60 Vdc V _{CB} = 100 Vdc		I _{CBO}		100 100	uAdc uAdc
⊛_ 3151	Thermal resistance (junction-to-case)	***		e ^{J-C}		35	°C/W
	Subgroup 2	•	λ=10			i	
1031	High-temperature life (non-operating)	T _{stg} = +200°C t = 1000 hours 3/		***	****		
3036	End-point tests: Collector-base cutoff current:	Bias Cond. D					
	2N1479, 2N1481 2N1480, 2N1482	V _{CB} =30 Vdc V _{CB} =50 Vdc		CBO CBO			uAdc uAdc
3076	Static forward-current transfer ratio:	I _C =200 mAdc V _{CE} =4 Vdc					
	2N1479, 2N1480 2N1481, 2N1482			h _{FE} h _{FE}	15 25	75 125	

Table III. Group C inspection. 1/-(Cont'd)

Test Method per	Examination or test	Conditions	LTPD Symbol	Limits	Unit
MIL-STD-750	<u>2</u> /		•	Min Max	
	Subgroup 3		λ=10		
1026	Steady-state operation life	T _A = +25°C V _{CE} = 28 Vdc P _T = 1.0 W t = 1000 hrs 3/			tou our new
	End-point tests Same as for Subgroup 2 above				
	Subgroup 4		10		
1026	Steady-state operation life:	T_{C} = +125°-0° C V_{CE} = 24 Vdc P_{T} = 2.15 W With heat sink t = 250 hours			
	End-point tests: Same as for Subgroup 2 above				
1/ Periodicity:	See 4.2.3 herein.	·			

2/ See 3.4 and 4.3.1 herein.



DIMENSIONS						
LTR	INC	HES	MILLIM	ETERS	Z Oトーਜ਼ぃ	
	MIN	MAX	MIN	MAX	S	
A	.335	.370	8.51	9.40		
В	.305	.335	7.75	8.51		
C	.240	.260	6.10	6.60		
D	1.500	1.750	3.81	4,45	9	
E	.016	:021	.41	•53	2,9	
F	.016	.019	.41	.48	3,9	
G	.100		2.54	~	4	
H					5	
7	.029	.045	.74	1.14	8	
K	.028	.034	.71	.86		
L.	.009	.125	.23	3.18		
M	.1414	Nom	3.59 1	Vom	6	
N	.0707	Nom	1.80 1	6		

NOTES:

- 1. Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 inm.
- 2. Measured in the zone beyond .250 (6.35 mm) from the seating plane.
- 3. Measured in the zone .050 (1.27 mm) and .250 (6.35 mm) from the seating plane.
- 4. Variations on Dim B in this zone shall not exceed .010 (.25 mm).
- 5. Outline in this zone is not controlled.
- 6. When measured in a gaging plane .054+.001 (1.37 mm +.03 mm) below the scaling plane of the transistor max dia leads shall be within .007 (.18 mm) of their true location relative to a maximum width tab. Smaller dia leads shall fall within the outline of the max dia lead tolerance.
 7. Collector internally connected to case.
- 8. Measured from the maximum diameter of the actual device.
- 9. All 3 leads.

Figure 1. Outline and dimensions.

5. PREPARATION FOR DELIVERY

5.1 <u>Preparation for delivery.</u> Preparation for delivery, and the inspection of preparation for delivery, shall be in accordance with Specification MIL-S-19500.

6. NOTES

6.1 Notes. - The notes included in Specification MIL-S-19500, with the following additions or exceptions, are applicable to this document.

6.2 Application guidance.-

- a. The revised requirements in this document issue do not impair ready, bilateral replaceability between the transistor covered herein and the transistors, respectively, as covered in the previous issue(s) of this document.
- b. To insure proper circuit application, particular attention should be given to the differential voltage-and-current requirements, ratings, and performance characteristics pertinent to the individual transistor types covered herein.

6.3 Ordering data.-

- a. Terminal-lead length (if other than as show in Fig. 1 herein): See 3.3.2 herein.
- 6.4 Qualification. With respect to products requiring qualification, awards will be made only for such products as have, prior to the time set for opening of bids, been tested and approved for inclusion in Qualified Products List (QPL)-19500, whether or not such products have actually been so listed by that date. Information pertaining to qualification of Products covered by this specification should be requested from the Commanding General, U. S. Army Electronics Command, Fort Monmouth, New Jersey 07703, attention: AMSEL-PP-EM-2.
- o.5 Changes from previous issue. The margins of this document are marked with an asterisk to indicate where changes (additions, modifications, corrections, deletions) from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

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Preparing activity:
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Project No. 5961-A083

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SPECIFICATION ANALYSIS SHEET

Form Approved Budget Bureau No. 119-R004

INSTRUCTIONS

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